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PATENT APPLICATION
RESPONSE UNDER 37 CFR §1.116
EXPEDITED PROCEDURE
TECHNOLOGY CENTER ART UNIT 1675

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Takao ABE et al.

Group Art Unit: 1765

Application No.: 09/743,982

Examiner: M.A. Anderson

Filed: January 18, 2001

Docket No.: 108360

For: SILICON SINGLE CRYSTAL AND WAFER DOPED WITH GALLIUM AND
METHOD FOR PRODUCING THEM

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the February 4, 2003 Office Action, please amend the above-identified
application as follows:

IN THE CLAIMS:

Please replace claims 35-45 as follows:

5201 > 35. (Twice Amended) The silicon single crystal solar cell according to Claim 30,
wherein loss of overall conversion efficiency due to photo-degradation is 0.5 % or less.

C 36. (Twice Amended) The silicon single crystal solar cell according to Claim 32,
wherein loss of overall conversion efficiency due to photo-degradation is 0.5 % or less.

37. (Twice Amended) A method for production of silicon single crystal to which
Ga is added according to Czochralski method wherein Ga is added in a silicon melt in a
crucible, a seed crystal is brought into contact with the silicon melt and is pulled with rotating

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